

**1. Scope :**

This specification applies to PIN silicon photodiode chips,  
Device No. PD-3061

**2. Structure :**

- 2-1. Planar type : PIN diode.
- 2-2. Electrodes :  
 Top side (Anode ) : Aluminum alloy .  
 Top side (Cathode) : Aluminum alloy .

**3. Size :**

- 3-1. Chip size : 63 mils × 63 mils (1.6 mm × 1.6 mm ).
- 3-2. Chip thickness : 12 ± 1.5mils (0.305 ± 0.038 mm).
- 3-3. Active area : 53 mils × 53 mils (1.346 mm × 1.346 mm ).
- 3-4. Bonding pad (Anode ) : 6 mils × 6 mils (0.153mm × 0.153 mm )  
 (Cathode ) : 6 mils × 6 mils (0.153mm × 0.153 mm )
- 3-5. Pattern drawing : Refer to the attached drawing.

**4. Electro-optical characteristics (Ta = 25 °C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse dark current	$I_D$	$V_R=10V$ $E_e=0mW/cm^2$			10	nA
Reverse breakdown voltage	$V_{(BR)R}$	$I_R=100\mu A$ $E_e=0mW/cm^2$	60			V
Open circuit voltage	$V_{oc}$	$T=2856K$ $E_e=5mW/cm^2$		410		mV
Short circuit Current	$I_{sc}$	$T=2856K$ $E_e=5mW/cm^2$		21		$\mu A$
Reverse light current	$I_L$	$V_R =5V$ $T=2856K$ $E_e=5mW/cm^2$		21		$\mu A$
Total Capacitance	$C_t$	$V_R =5V$ $E_e=0mW/cm^2$ $f=1MHz$		19		pF
Turn-on/ Turn-off Time	$t_{on}/t_{off}$	$V_R=5V$ $R_L=50\Omega$ $\lambda=850nm$		80/90		ns

\*Based on 100% probing

